

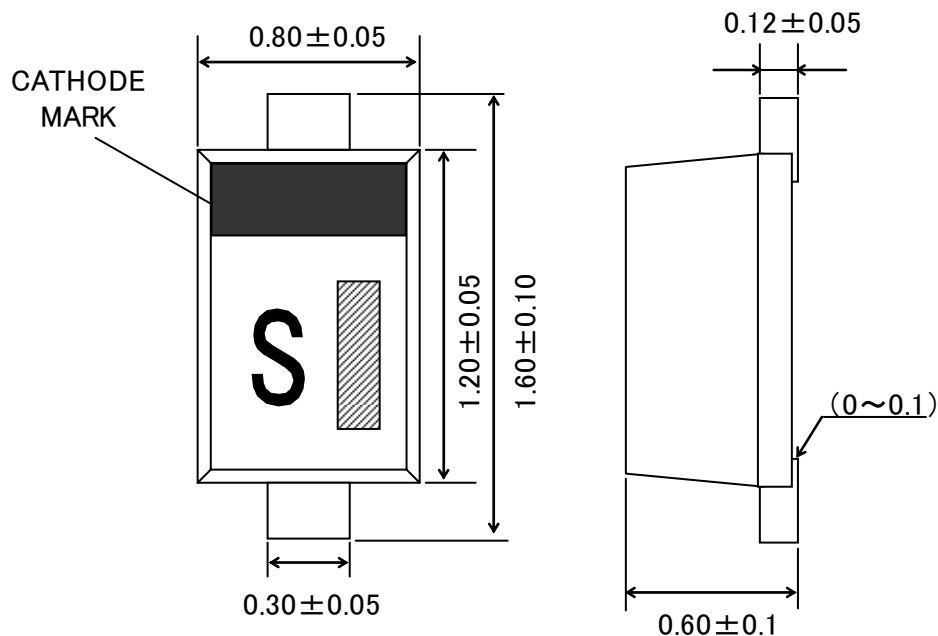
1. PRODUCT Schottky Barrier Diode (Silicon Epitaxial Planer)
2. TYPE RB521SM-40
3. APPLICATION Small current rectification
4. FEATURE
  - Ultra small mold type (EMD2)
  - High reliability
5. ABSOLUTE MAXIMUM RATING (Ta=25°C)
 

Reverse voltage (repetitive peak)	VRM	. . . . .	45 V
Reverse voltage (DC)	VR	. . . . .	40 V
Average rectified forward current	Io	. . . . .	200 mA
Forward current surge peak (t=1ms·1cyc.)	IFSM	. . . . .	4 A
Junction temperature	Tj	. . . . .	150 °C
Storage temperature	Tstg	. . . . .	-55~150 °C

6. ELECTRICAL CHARACTERISTIC (Ta=25°C)

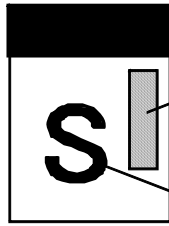
Characteristic	Symbol	Test condition	Standard		
			MIN.	TYP.	MAX.
Forward voltage	VF	IF= 10 mA	0.16 V	0.26 V	0.30 V
		IF= 100 mA	0.31 V	0.395 V	0.45 V
		IF= 200 mA	0.41 V	0.495 V	0.54 V
Reverse current	IR	VR= 10 V	-	3.5 μA	20 μA
		VR= 40 V	-	13 μA	90 μA

7. DIMENSION (UNIT:mm)



DESIGN	CHECK	APPROVAL	DATE:27.AUG.2010	SPECIFICATION No. : RB521SM40-E
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## 8. Marking



There is dot on the package which tells production year, week and its product manufacture.

「S」is the sign which shows RB521SM-40.

## Attention in use

Compared with PN junction diodes, Schottky Barrier Diode generally have higher IR (Reverse leakage current). So that the reverse loss of the diode will increase as temperature increase causing heat up and resulting further increase of IR.

This phenomenon will be cause of over heat destruction of the diode.

This product is low VF(Forward voltage) type diode and have higher IR compared with the other diodes, because VF and IR characteristics are contrary to each other.

Therefore please give consideration to the reverse loss and around temperature when using this product.